

POWER SCHOTTKY RECTIFIER

MAIN PRODUCT CHARACTERISTICS

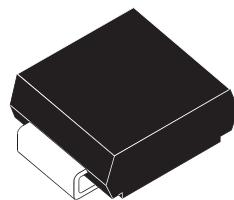
$I_{F(AV)}$	3 A
V_{RRM}	40 V
$T_j(\text{max})$	150°C
$V_F(\text{max})$	0.44 V

FEATURES AND BENEFITS

- NEGLIGIBLE SWITCHING LOSSES
- LOW THERMAL RESISTANCE
- LOW FORWARD VOLTAGE DROP
- AVALANCHE CAPABILITY SPECIFIED

DESCRIPTION

Schottky rectifier suited for Switched Mode Power Supplies and high frequency DC to DC converters. Packaged in SMC, this device is intended for use in DC/DC chargers.



SMC
(JEDEC DO-214AB)

ABSOLUTE RATINGS (limiting values)

Symbol	Parameter	Value	Unit
V_{RRM}	Repetitive peak reverse voltage	40	V
$I_{F(RMS)}$	RMS forward current	10	A
$I_{F(AV)}$	Average forward current	3	A
I_{FSM}	Surge non repetitive forward current	75	A
I_{RRM}	Repetitive peak reverse current	1	A
P_{ARM}	Repetitive peak avalanche power	1300	W
T_{stg}	Storage temperature range	- 65 to + 175	°C
T_j	Maximum operating junction temperature *	150	°C
dV/dt	Critical rate of rise of reverse voltage	10000	V/μs

* : $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th}(j - a)}$ thermal runaway condition for a diode on its own heatsink

STPS3L40S

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-l)}$	Junction to leads	18	°C/W

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Tests conditions		Typ.	Max.	Unit
I_R *	Reverse leakage current	$T_j = 25^\circ\text{C}$	$V_R = V_{RRM}$		100	μA
		$T_j = 125^\circ\text{C}$		16	40	mA
V_F *	Forward voltage drop	$T_j = 25^\circ\text{C}$	$I_F = 3 \text{ A}$		0.5	V
		$T_j = 125^\circ\text{C}$	$I_F = 3 \text{ A}$	0.40	0.44	
		$T_j = 25^\circ\text{C}$	$I_F = 6 \text{ A}$		0.62	
		$T_j = 125^\circ\text{C}$	$I_F = 6 \text{ A}$	0.52	0.58	

Pulse test : * $t_p = 380 \mu\text{s}$, $\delta < 2\%$

To evaluate the maximum conduction losses use the following equation :
 $P = 0.30 \times I_{F(AV)} + 0.047 I_{F}^2(\text{RMS})$

Fig. 1: Average forward power dissipation versus average forward current.

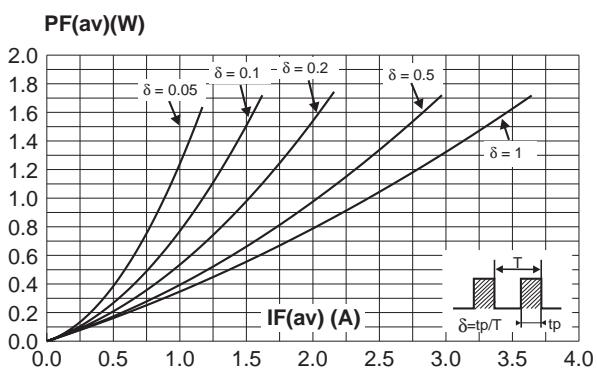


Fig. 2: Average forward current versus ambient temperature ($\delta = 0.5$).

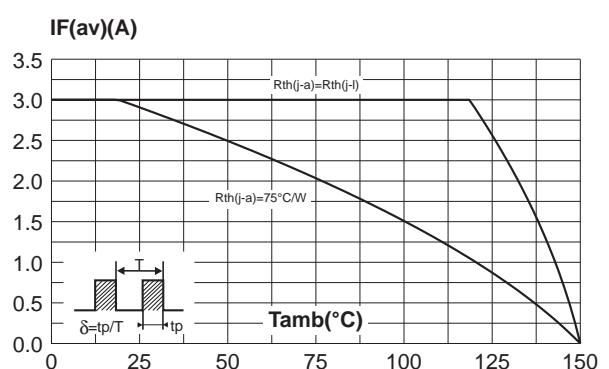


Fig. 3: Normalized avalanche power derating versus pulse duration.

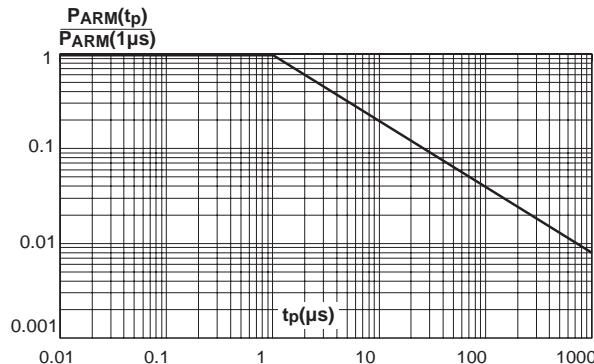


Fig. 5: Non repetitive surge peak forward current versus overload duration (maximum values).

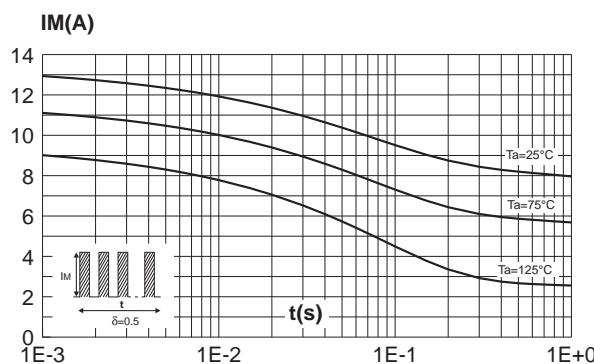


Fig. 7: Reverse leakage current versus reverse voltage applied (typical values).

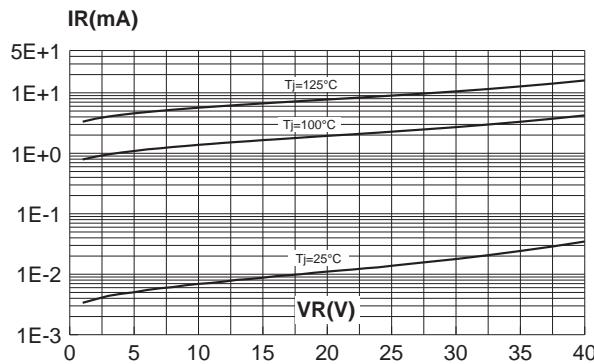


Fig. 4: Normalized avalanche power derating versus junction temperature.

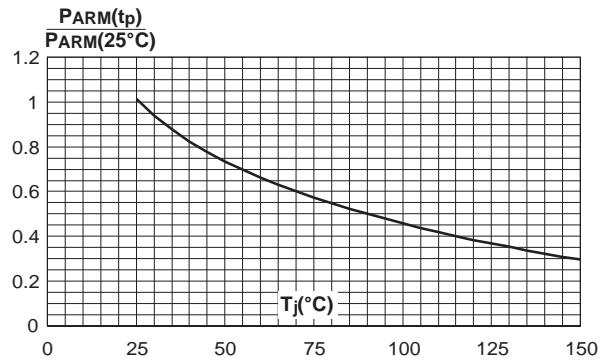


Fig. 6: Relative variation of thermal impedance junction to ambient versus pulse duration (epoxy printed circuit board, e(Cu)=35μm, recommended pad layout).

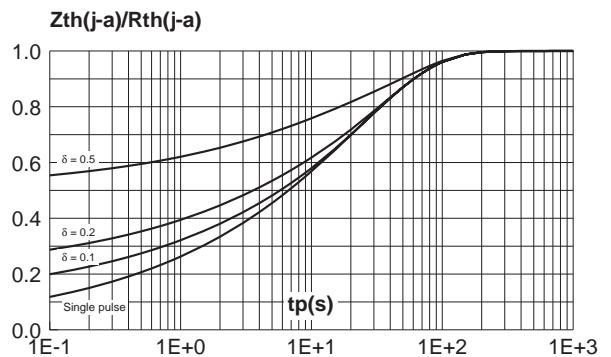
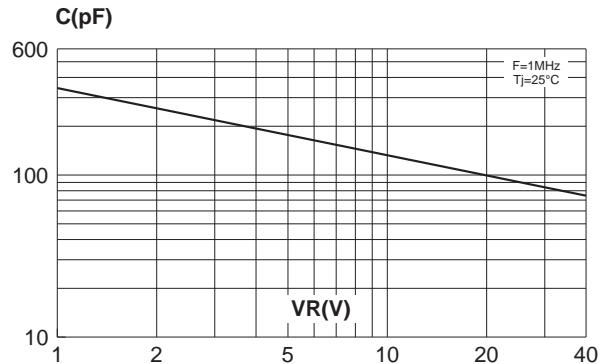


Fig. 8: Junction capacitance versus reverse voltage applied (typical values).



STPS3L60S

Fig. 9: Forward voltage drop versus forward current (maximum values).

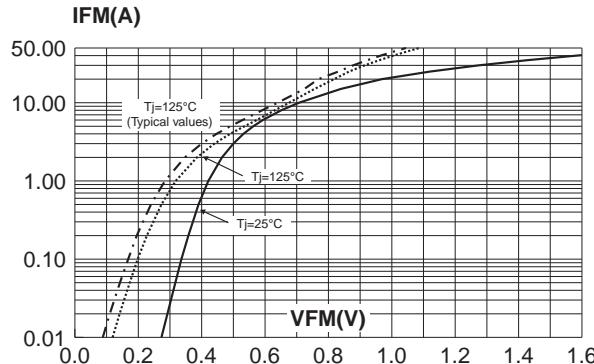


Fig. 10: Non repetitive surge peak forward current versus number of cycles.

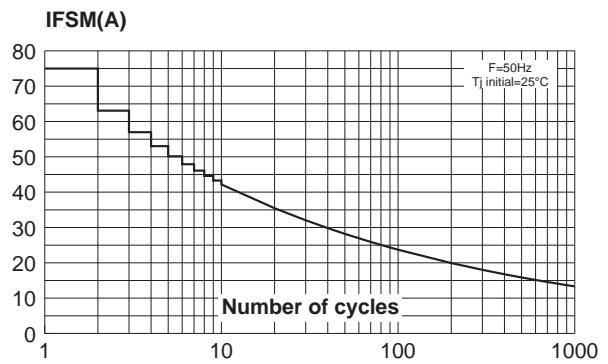
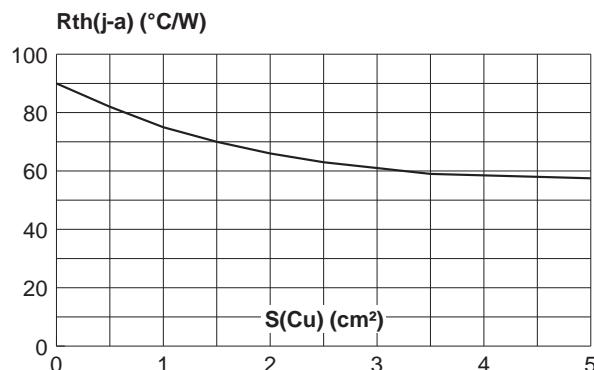
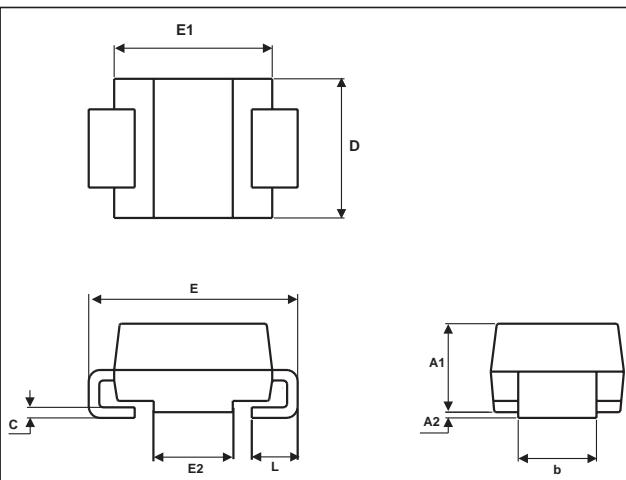


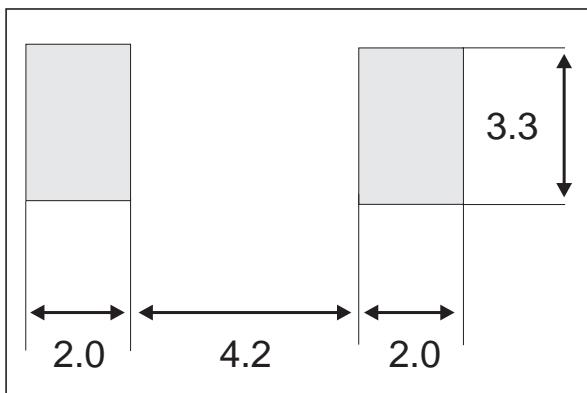
Fig. 11: Thermal resistance junction to ambient versus copper surface under tab (Epoxy printed circuit board FR4, copper thickness: 35 μm).



PACKAGE MECHANICAL DATA
 SMC



REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A1	1.90	2.45	0.075	0.096
A2	0.05	0.20	0.002	0.008
b	2.90	3.2	0.114	0.126
c	0.15	0.41	0.006	0.016
E	7.75	8.15	0.305	0.321
E1	6.60	7.15	0.260	0.281
E2	4.40	4.70	0.173	0.185
D	5.55	6.25	0.218	0.246
L	0.75	1.60	0.030	0.063

FOOT PRINT (in millimeters)

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STPS3L40S	S3L4	SMC	0.24g	2500	Tape and reel

- EPOXY MEETS UL94,V0
- BAND INDICATES CATHODE

Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied.
STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

The ST logo is a registered trademark of STMicroelectronics

© 2003 STMicroelectronics - Printed in Italy - All rights reserved.

STMicroelectronics GROUP OF COMPANIES

Australia - Brazil - Canada - China - Finland - France - Germany
 Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Singapore
 Spain - Sweden - Switzerland - United Kingdom - United States.

<http://www.st.com>